

Title (en)

METHOD AND DEVICE FOR PLATING A RECESS IN A SUBSTRATE

Title (de)

VERFAHREN UND VORRICHTUNG ZUR PLATTIERUNG EINER VERTIEFUNG IN EINEM SUBSTRAT

Title (fr)

PROCÉDÉ ET DISPOSITIF DE PLACAGE D'UN ÉVIDEMENT DANS UN SUBSTRAT

Publication

EP 3517656 A3 20191016 (EN)

Application

EP 19150854 A 20190108

Priority

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Abstract (en)

The invention relates to a method for plating a recess in a substrate, a device for plating a recess in a substrate and a system for plating a recess in a substrate comprising the device. The method for plating a recess in a substrate comprises the following steps:a) Providing a substrate with a substrate surface comprising at least one recess,b) applying a replacement gas to the recess to replace an amount of ambient gas in the recess to at least partially clear the recess from the ambient gas,c) applying a processing fluid to the recess, wherein the replacement gas dissolves in the processing fluid to at least partially clear the recess from the replacement gas, andd) plating the recess.

IPC 8 full level

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Citation (search report)

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US 11164748 B2 20211102; US 11908698 B2 20240220; US 2019228975 A1 20190725; US 2022020591 A1 20220120

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